NTMFS4707N

Power MOSFET
30 V, 17 A, Single N−Channel, SOIC−8 Flat Lead

ON Semiconductor®

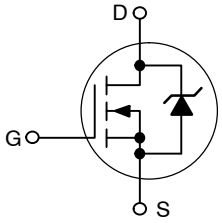
http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
30 V	10 mΩ @ 10 V	17 A
	13.5 mΩ @ 4.5 V	

Features
- Fast Switching Times
- Low Gate Charge
- Low $R_{DS(on)}$
- Low Inductance SOIC−8 Package
- These are Pb−Free Devices

Applications
- Notebooks, Graphics Cards
- DC−DC Converters
- Synchronous Rectification

N−Channel



MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

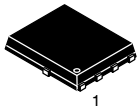
Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	10.2	A
		T_A = 85°C		7.4	
	t ≤ 10 s	T_A = 25°C		17	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	2.3	W
	t ≤ 10 s			6.25	
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	6.9	A
		T_A = 85°C		4.9	
Power Dissipation (Note 2)		T_A = 25°C	P_D	1.0	W
Pulsed Drain Current	t_p ≤ 10 μs		I_{DM}	51	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	6.25	A
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 25 V, V_{GS} = 10 V, I_{PK} = 7.0 A, L = 10 mH, R_G = 25 Ω)			E_{AS}	245	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	55	°C/W
Junction−to−Ambient − t ≤ 10 s (Note 1)	$R_{\theta JA}$	20	
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	122.5	

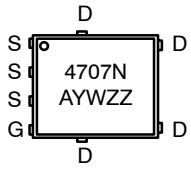
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface−mounted on FR4 board using the minimum recommended pad size (Cu area = 0.412 in sq).



SOIC−8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM & PIN ASSIGNMENT



4707N = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4707NT1G	SOIC−8 FL (Pb−Free)	1500 / Tape & Reel
NTMFS4707NT3G	SOIC−8 FL (Pb−Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				6.5		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			50	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.0		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				5.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 10 A			10	13	mΩ
		V_{GS} = 4.5 V, I_D = 8.0 A			13.5	17	
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 10 A			20		S
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 24 V			735		pF
Output Capacitance	C_{OSS}				295		
Reverse Transfer Capacitance	C_{RSS}				80		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V; I_D = 10 A			7.5	15	nC
Threshold Gate Charge	$Q_{G(TH)}$				1.1		
Gate−to−Source Charge	Q_{GS}				2.0		
Gate−to−Drain Charge	Q_{GD}				3.6		
Gate Resistance	R_G				2.4		Ω
SWITCHING CHARACTERISTICS (Note 4)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = 10 V, V_{DD} = 15 V, I_D = 1.0 A, R_G = 3.0 Ω			6.0		ns
Rise Time	t_r				5.0		
Turn−Off Delay Time	$t_{d(off)}$				19		
Fall Time	t_f				11		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 6.25 A	T_J = 25°C		0.79	1.0	V
			T_J = 125°C		0.59		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, d_{IS}/d_t = 100 A/μs, I_S = 6.25 A			26		ns
Charge Time	t_a				14		
Discharge Time	t_b				12		
Reverse Recovery Charge	Q_{RR}				19		nC

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERIZATIONS

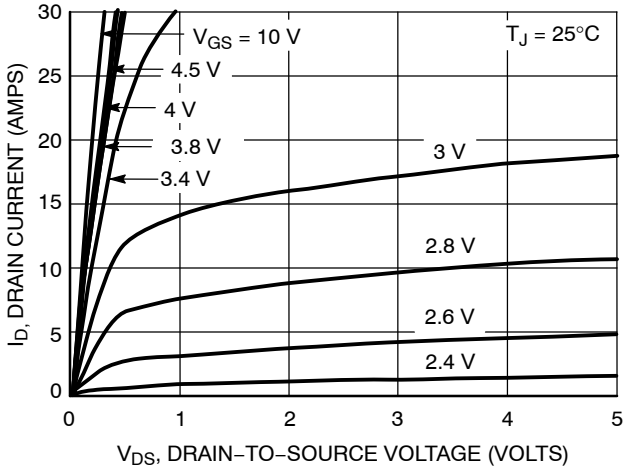


Figure 1. On−Region Characteristics

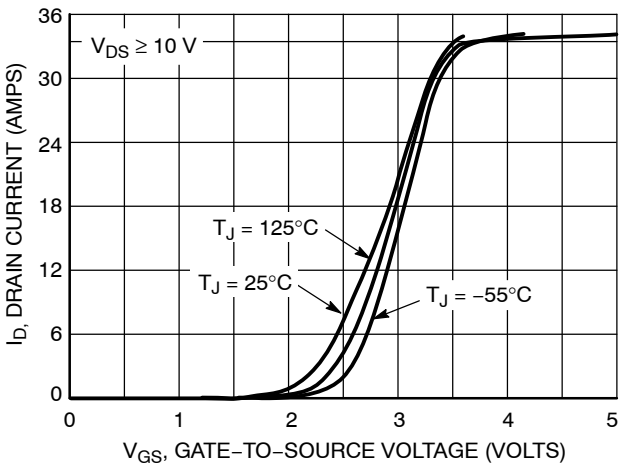


Figure 2. Transfer Characteristics

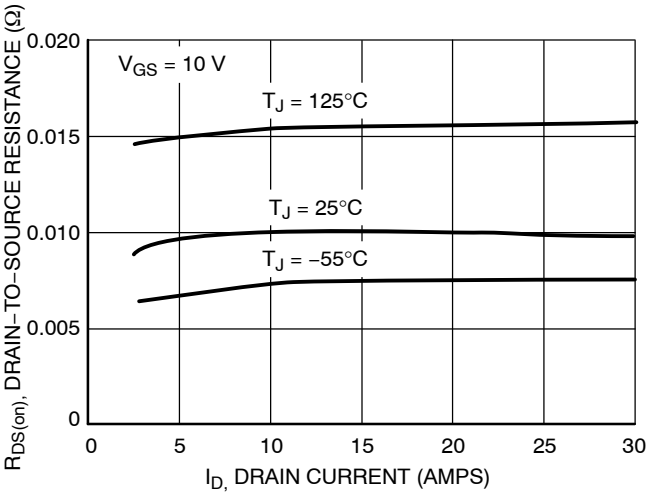


Figure 3. On−Resistance vs. Drain Current and Temperature

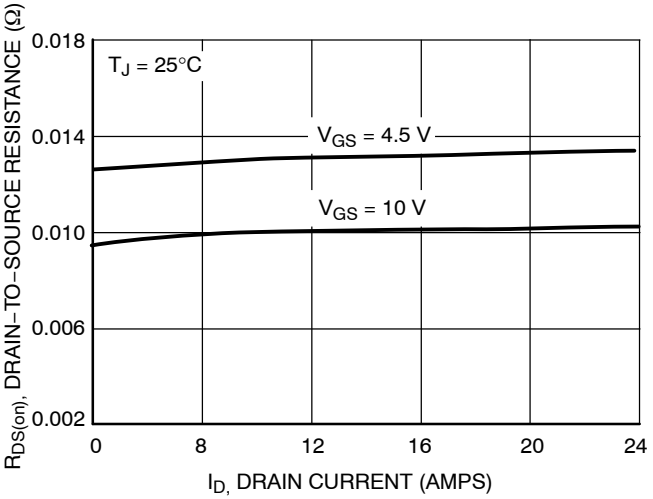


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

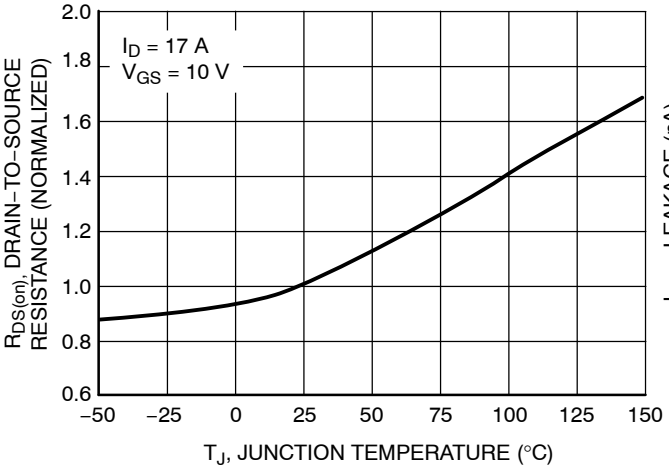


Figure 5. On−Resistance Variation with Temperature

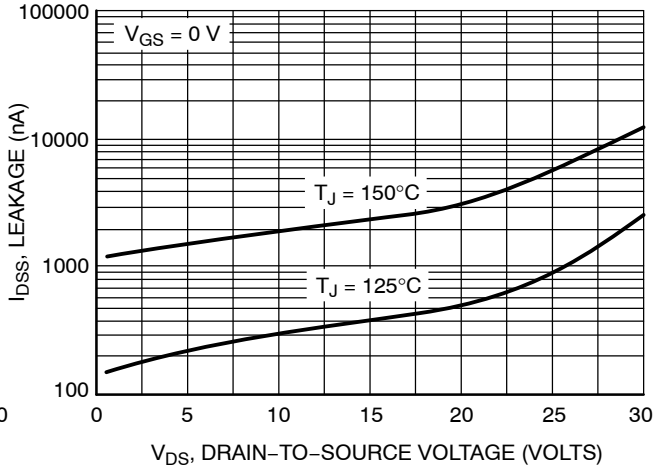


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERIZATIONS

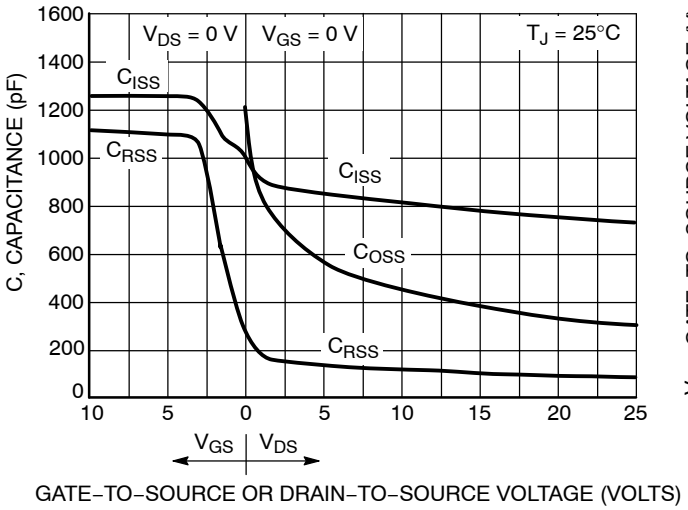


Figure 7. Capacitance Variation

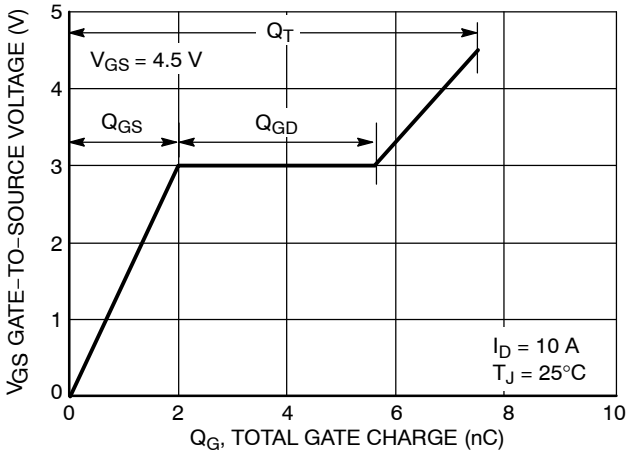


Figure 8. Gate−To−Source and Drain−To−Source Voltage vs. Total Charge

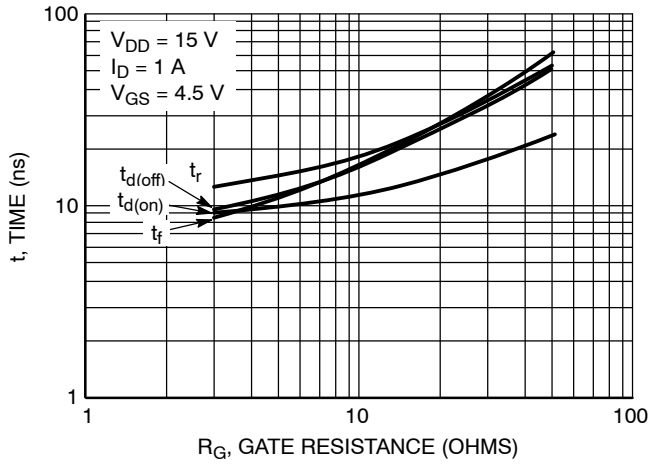


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

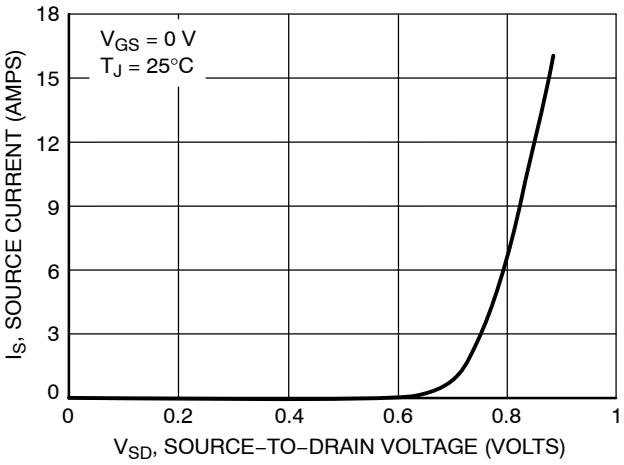


Figure 10. Diode Forward Voltage vs. Current

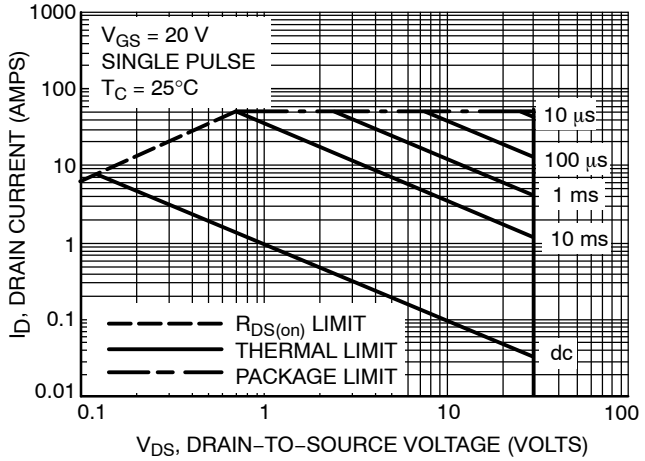


Figure 11. Maximum Rated Forward Biased Safe Operating Area

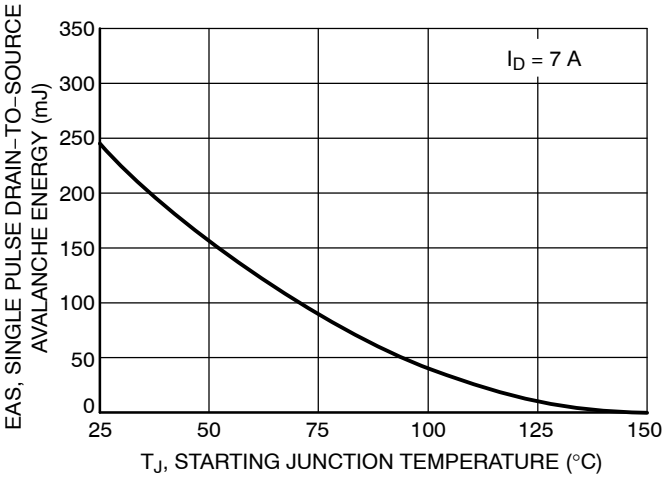
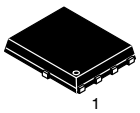


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

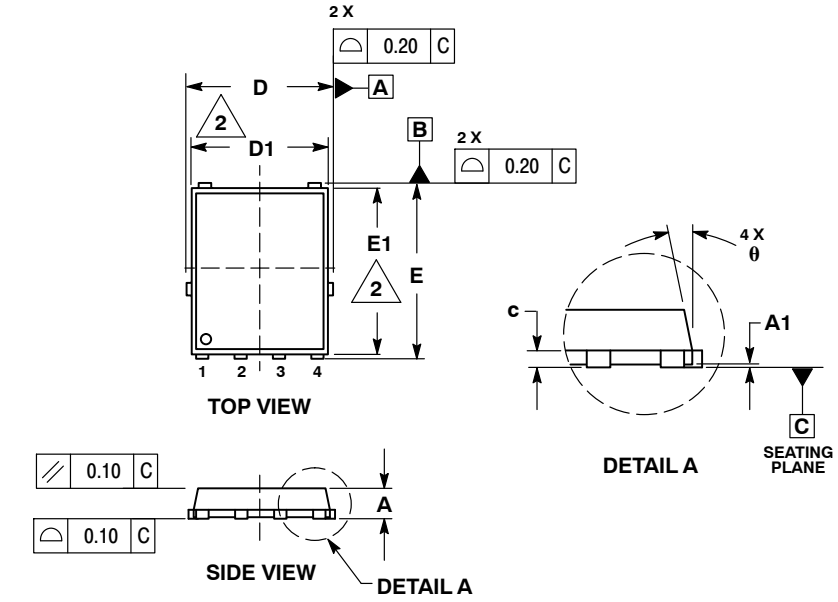
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 2:1

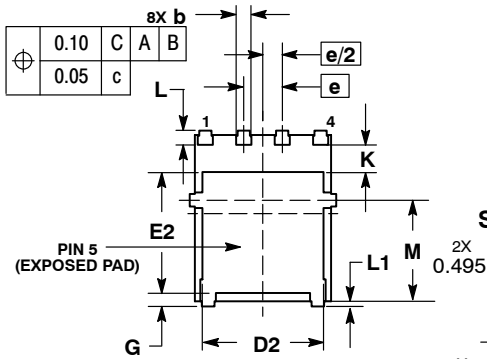
DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

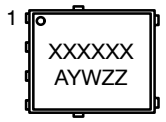


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	–––	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	–––	12 °



GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
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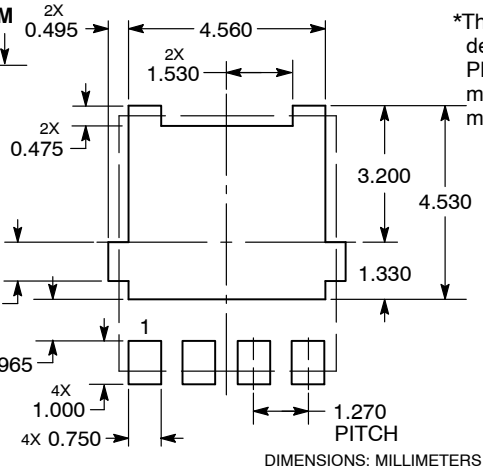
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	**DFN5 5x6, 1.27P (SO−8FL)**	**PAGE 1 OF 1**

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